

600V, 20A, Trench FS II IGBT

General Description:

Using NCE's proprietary trench design and advanced FS (field stop) second generation technology, the 600V Trench FSIIIGBT offers superior conduction and switching performances, and easy parallel operation;

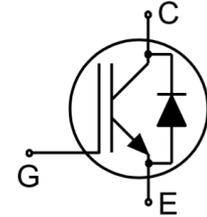
Features

Trench FSII Technology offering

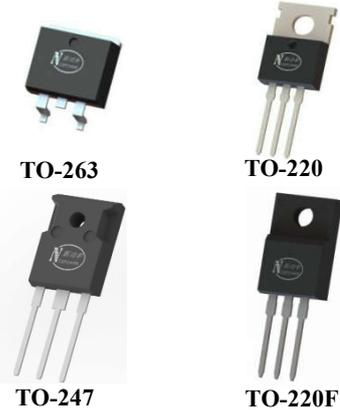
- Very low $V_{CE(sat)}$
- High speed switching
- Positive temperature coefficient in $V_{CE(sat)}$
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

Application

- Uninterruptible Power Supplies (UPS)
- Welding Converters
- Inverters



Schematic diagram



Package Marking and Ordering Information

Device	Device Package	Device Marking
NCE20TD60D	TO-263	NCE20TD60D
NCE20TD60	TO-220	NCE20TD60

Device	Device Package	Device Marking
NCE20TD60F	TO-220F	NCE20TD60F
NCE20TD60T	TO-247	NCE20TD60T

Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	NCE20TD60D NCE20TD60 NCE20TD60T	NCE20TD60F	Units
V_{CES}	Collector-Emitter Voltage	600		V
V_{GES}	Gate- Emitter Voltage	±30		V
I_C	Collector Current	40	40*	A
	Collector Current @ $T_C = 100^\circ\text{C}$	20	20*	A
I_{Cplus}	Pulsed Collector Current, t_p limited by T_{jmax}	80	45	A
-	turn off safe operating area, $V_{CE}=600V, T_j=150^\circ\text{C}$	80	45	A
I_F	Diode Continuous Forward Current @ $T_C = 100^\circ\text{C}$	10	20*	A
I_{FM}	Diode Maximum Forward Current	80	80	A
P_D	Power Dissipation @ $T_C = 25^\circ\text{C}$	166	86	W
	Power Dissipation @ $T_C = 100^\circ\text{C}$	67	35	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	-55 to +150		°C
T_L	Maximum Temperature for Soldering	260		°C
t_{sc}	Short circuit withstand time $V_{GE}=15.0V, V_{CC} \leq 400V$, Allowed number of short circuits<1000Time between short circuits: $\geq 1.0s, T_j \leq 150^\circ\text{C}$	10		us

Thermal Characteristic

Symbol	Parameter	NCE20TD60D NCE20TD60 NCE20TD60T	NCE20TD60F	Units
R _{θJC}	Thermal Resistance, Junction to case for IGBT	0.75	1.45	°C/W
R _{θJC}	Thermal Resistance, Junction to case for Diode	1.88	3.9	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	62	78	°C/W

Electrical Characteristics (T_C=25°C unless otherwise noted)

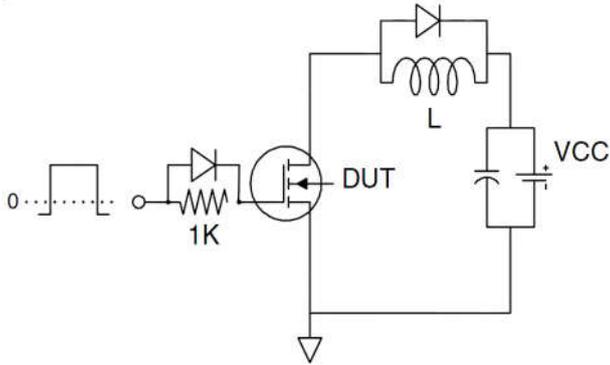
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
OFF Characteristics						
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	V _{GE} =0V, I _{CE} =1mA	600	--	--	V
I _{CES}	Collector-Emitter Leakage Current	V _{GE} =0V, V _{CE} =600V	--	--	4	uA
I _{GES(F)}	Gate to Emitter Forward Leakage	V _{GE} =+30V, V _{CE} =0V	--	--	100	nA
I _{GES(R)}	Gate to Source Reverse Leakage	V _{GE} =-30V, V _{CE} =0V	--	--	100	nA
ON Characteristics						
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C =20A, V _{GE} =15V	--	1.7	1.9	V
V _{GE(th)}	Gate Threshold Voltage	I _C =1mA, V _{CE} =V _{GE}	4.0	5.0	6.0	V
Dynamic Characteristics						
C _{ies}	Input Capacitance	V _{CE} =25V, V _{GE} =0V, f=1MHz	--	950	--	pF
C _{oes}	Output Capacitance		--	75	--	
C _{res}	Reverse Transfer Capacitance		--	52	--	
Q _{Gate}	Gate charge	V _{CC} =480V, I _C =20A V _{GE} =15V	--	100	--	nC
I _{C(SC)}	Short circuit collector current Max.1000 short circuits Time between short circuits: ≥1.0s	V _{GE} =15V, V _{CC} ≤400V, t _{SC} ≤10us, T _J ≤150°C	--	100	--	A
Switching Characteristics						
t _{d(ON)}	Turn-on Delay Time	V _{CE} =400V, I _C =20A V _{GE} =0/15V, R _g =15Ω Inductive Load	--	30	--	ns
t _r	Rise Time		--	18	--	
t _{d(OFF)}	Turn-Off Delay Time		--	176	--	
t _f	Fall Time		--	40	--	
E _{on}	Turn-On Switching Loss		--	1.0	--	mJ
E _{off}	Turn-Off Switching Loss		--	0.4	--	
E _{ts}	Total Switching Loss		--	1.4	--	

Electrical Characteristics of the Diode (T_C= 25°C unless otherwise specified)

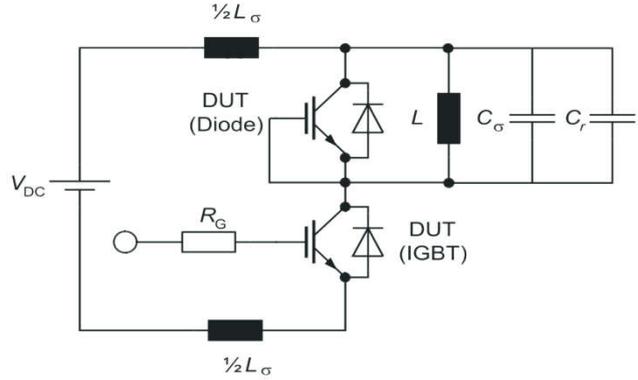
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V _{FM}	Diode Forward Voltage	I _F =10A	--	1.27	1.7	V
T _{rr}	Reverse Recovery Time	V _{CC} =400V, I _F =10A, di/dt=600A/uS	--	130	--	ns
I _{RRM}	Diode Peak Reverse Recovery Current		--	15	--	A
Q _{rr}	Reverse Recovery Charge		--	0.97	--	uC

Test Circuit

1) Gate Charge Test Circuit

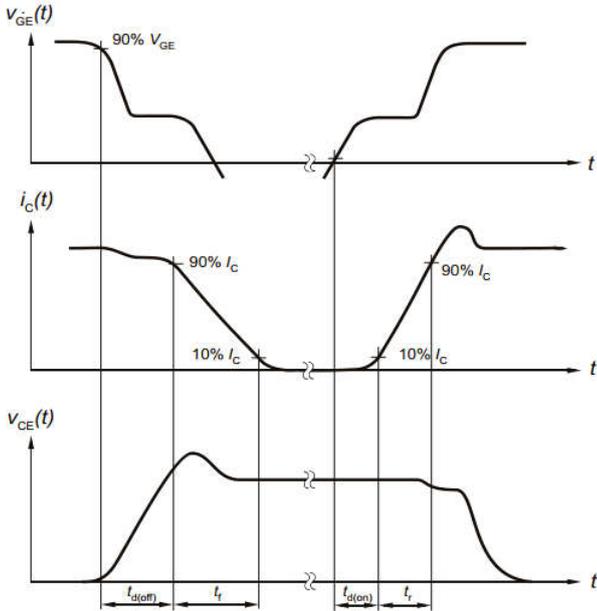


2) Switch Time Test Circuit

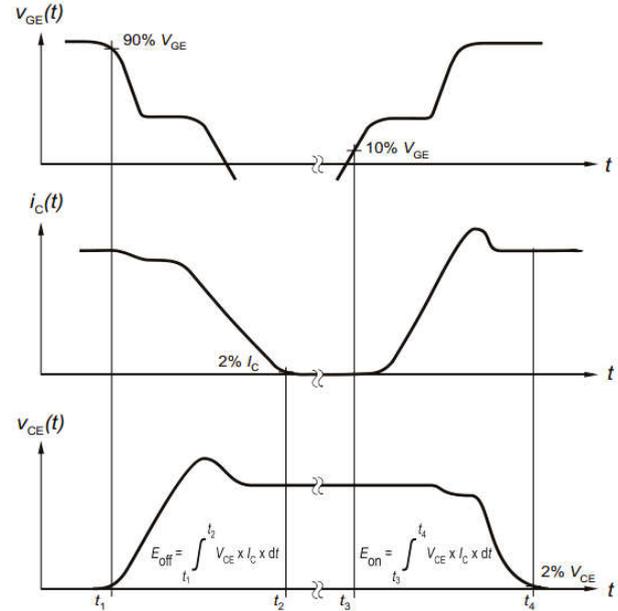


Switching characteristics

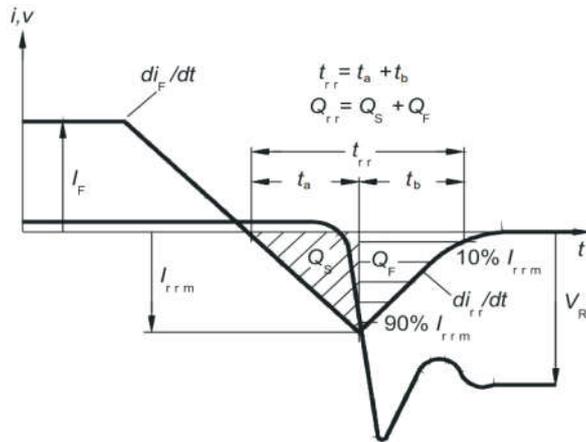
1) definition of switching times



2) definition of switching losses



3) Definition of diode switching characteristics



Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

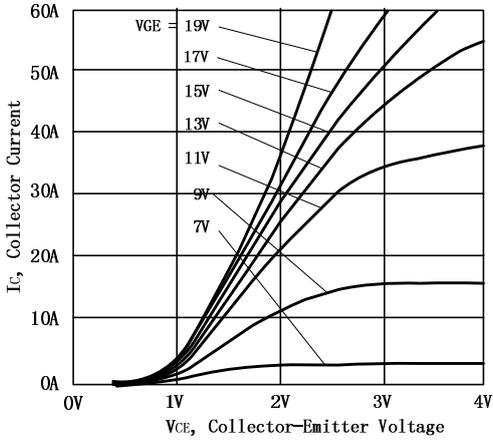


Figure 2. Transfer Characteristics

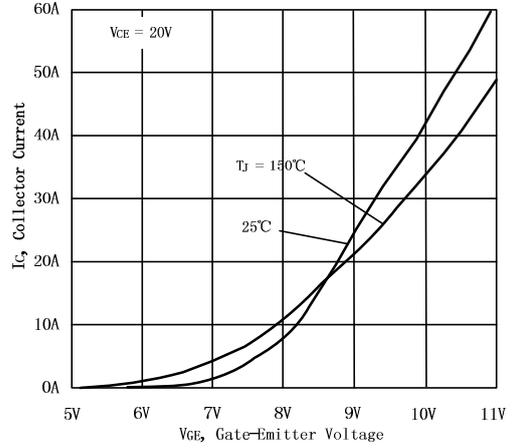


Figure 3 V_{CEsat} vs. Case Temperature

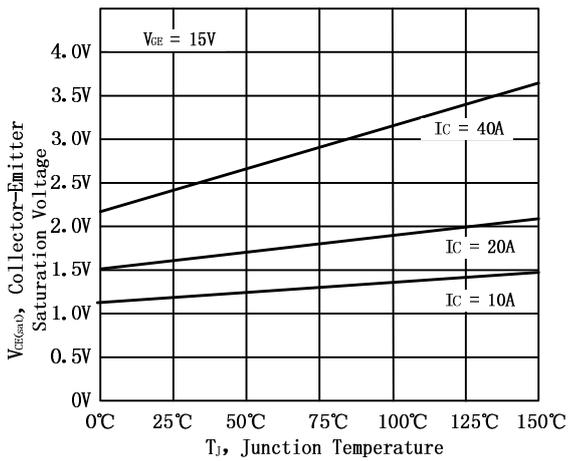


Figure 4 Saturation Voltage vs. VGE

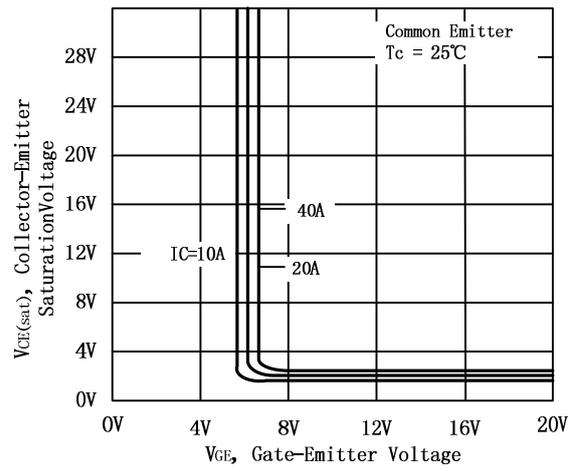


Figure 5 Capacitance Characteristics

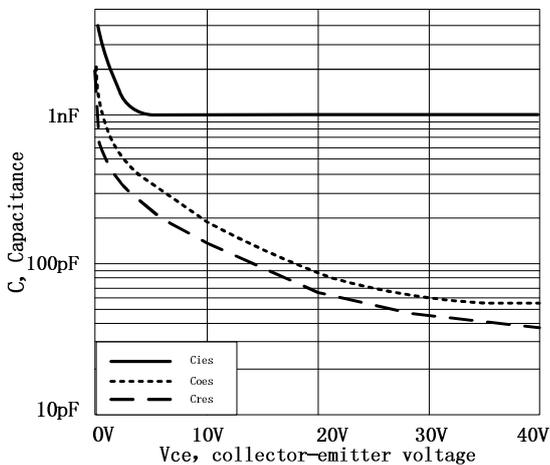
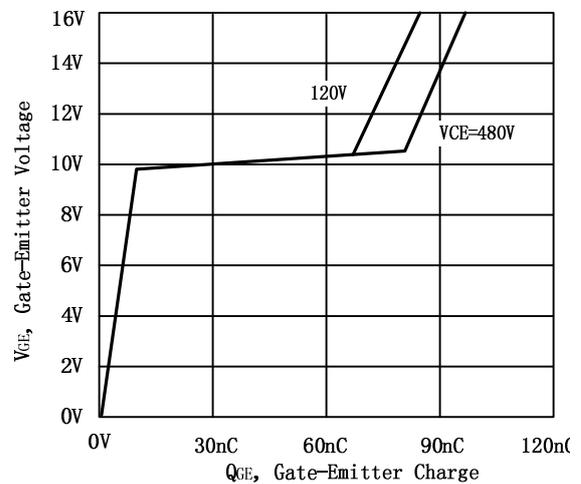


Figure 6 Gate charge waveform



Typical Electrical and Thermal Characteristics (continued)

Figure 7. Forward Characteristics

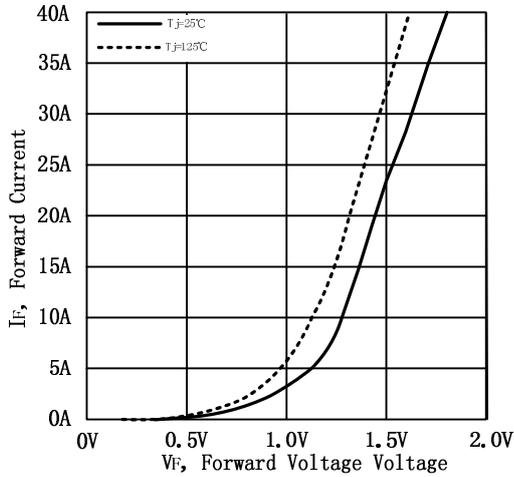


Figure 8 V_F vs. Temperature

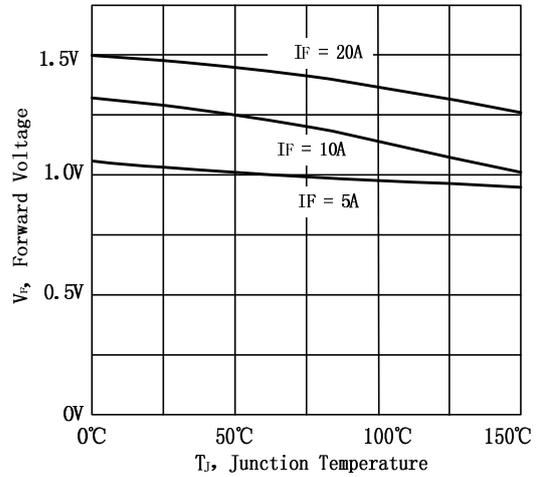


Figure 9. Transient Thermal Impedance of IGBT for TO-220F

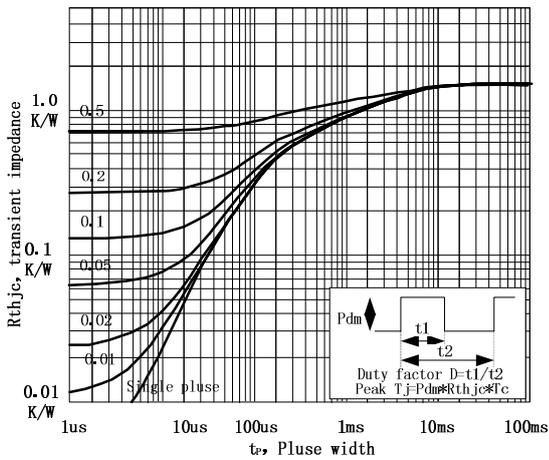
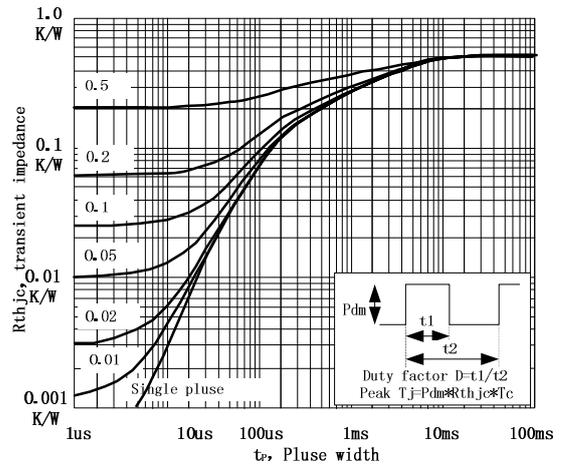
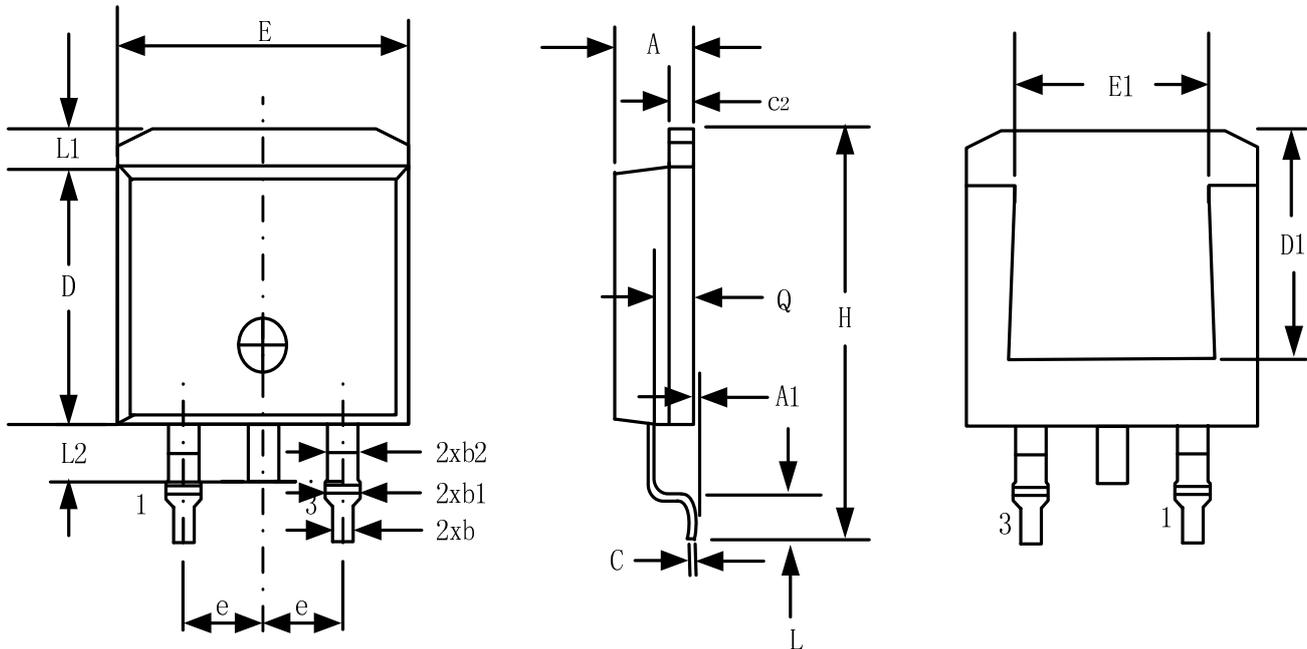


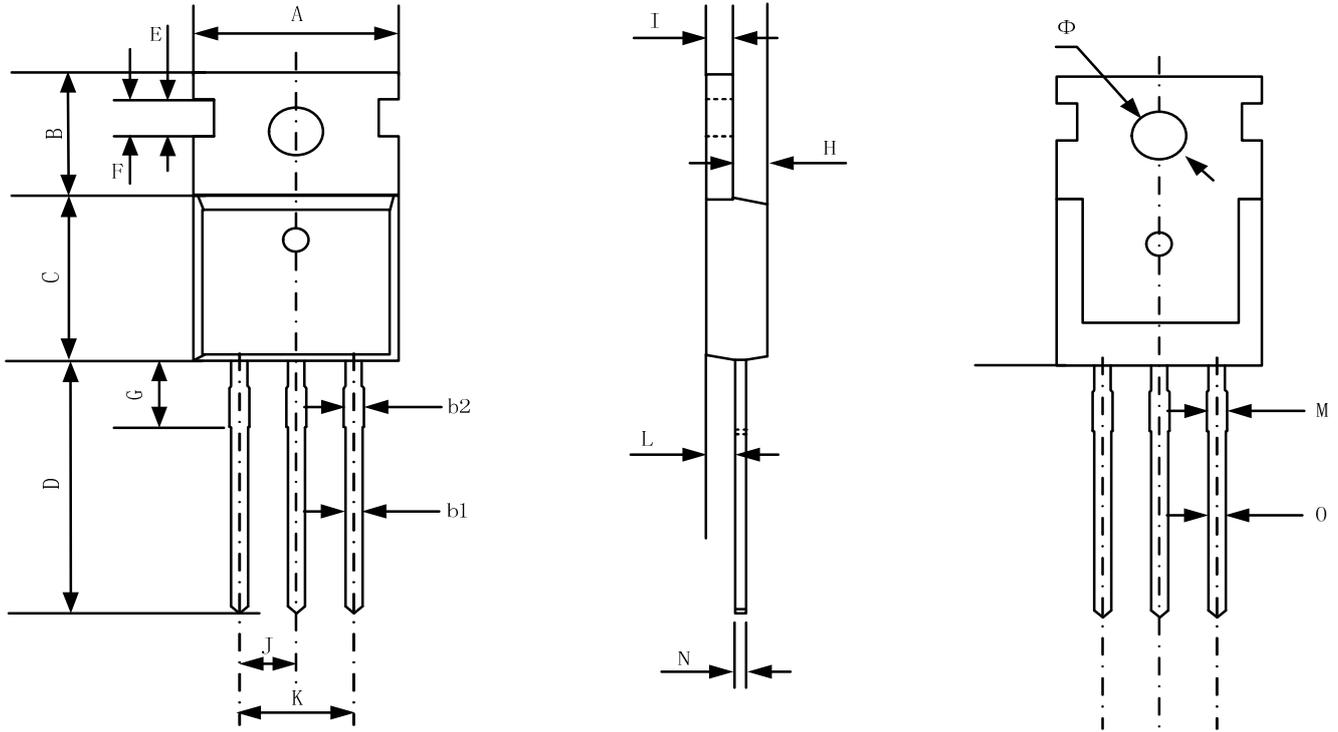
Figure 10. Transient Thermal Impedance of IGBT for TO-220, TO-263, TO-247



TO-263-3L Package Information


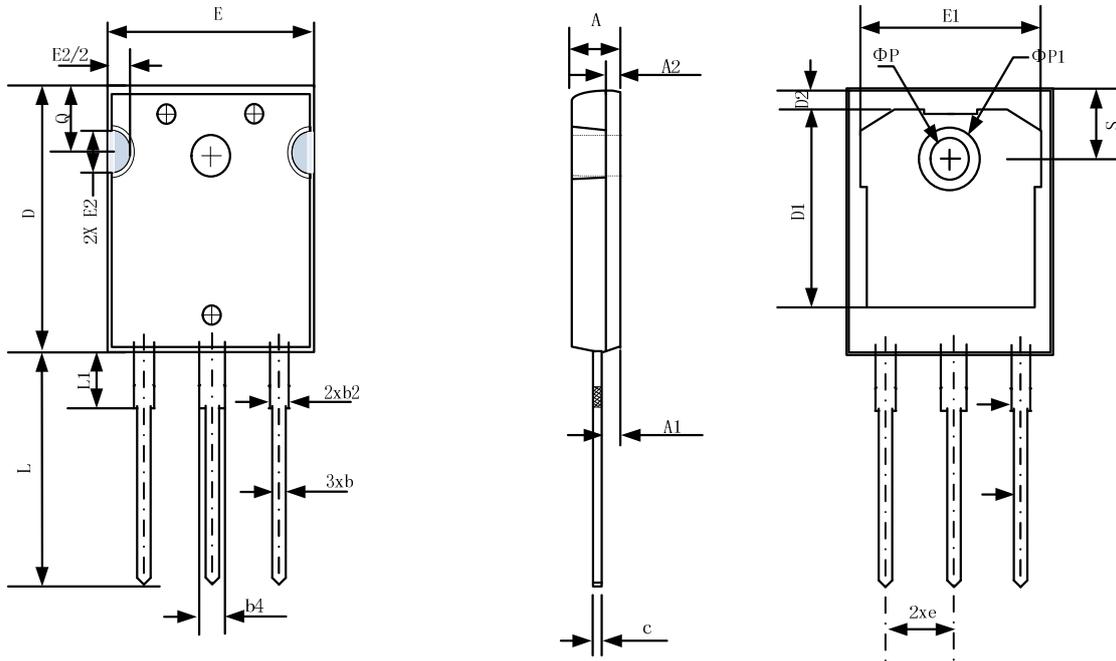
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.24	4.64	0.167	0.183
A1	0.00	0.25	0.000	0.010
b	0.70	0.90	0.028	0.035
b1	1.20	1.75	0.047	0.069
b2	1.20	1.70	0.047	0.067
C	0.40	0.60	0.016	0.024
c2	1.15	1.40	0.045	0.055
D	8.82	9.02	0.347	0.355
D1	6.86	--	0.270	--
E	9.96	10.36	0.392	0.408
E1	6.89	7.89	0.271	0.311
e	2.54 BSC		0.10 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.36 REF		0.054 REF	
L2	1.50 REF		0.059 REF	
L3	0.25 REF		0.010 REF	
Q	2.30	2.70	0.091	0.106

TO-220-3L-C Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	9.70	10.10	0.38	0.40
B	6.30	6.70	0.25	0.26
C	9.00	9.47	0.35	0.37
D	12.80	13.30	0.50	0.52
E	1.20	1.40	0.05	0.06
F	1.70 REF		0.067 REF	
G	2.65 REF		0.104 REF	
H	3.00	3.40	0.12	0.13
I	1.25	1.40	0.05	0.06
J	2.40	2.70	0.09	0.11
K	5.00	5.15	0.20	0.20
L	2.20	2.60	0.09	0.10
M	1.25	1.45	0.05	0.06
N	0.45	0.60	0.02	0.02
O	0.70	0.90	0.03	0.04
Φ	3.6 REF		0.142 REF	

TO-247-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	0.190	0.205
A1	2.29	2.55	0.090	0.100
A2	1.50	2.49	0.059	0.098
b	1.12	1.33	0.044	0.052
b2	1.91	2.39	0.075	0.094
b4	2.87	3.22	0.113	0.127
c	0.55	0.69	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.51	1.35	0.020	0.053
E	15.75	16.13	0.620	0.635
E1	13.46	14.16	0.530	0.557
E2	4.32	5.49	0.170	0.216
e	5.44 BSC		0.214 BSC	
L	19.81	20.32	0.780	0.800
L1	4.10	4.40	0.161	0.173
ΦP	3.56	3.65	0.140	0.144
ΦP1	7.19 REF		0.283 REF	
Q	5.39	6.20	0.212	0.244
S	6.04	6.30	0.238	0.248

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